

Publication

EP 0575003 A3 19940803

Application

EP 93201714 A 19930615

Priority

DE 4219649 A 19920616

Abstract (en)

[origin: EP0575003A2] The invention relates to a high-resistance electrical resistive layer having a low temperature coefficient, which contains carbon, hydrogen and metal, some of the carbon being optionally substituted by silicon, boron and/or nitrogen.

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H01C 17/06

IPC 8 full level

H01C 7/00 (2006.01); **H01C 17/06** (2006.01); **H01C 17/12** (2006.01)

CPC (source: EP US)

H01C 7/006 (2013.01 - EP US); **H01C 17/12** (2013.01 - EP US)

Citation (search report)

[A] GERHARD SOBE ET AL.: "Process characterization with D.C. magnetron sputtering of Cr-Si-C thin films in Ar-CH₄ mixtures", THIN SOLID FILMS, vol. 201, no. 1, 5 June 1991 (1991-06-05), LAUSANNE CH, pages 109 - 122

Cited by

US8198978B2; WO2009129930A1

Designated contracting state (EPC)

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EP 0575003 A2 19931222; **EP 0575003 A3 19940803**; **EP 0575003 B1 19990217**; DE 59309376 D1 19990325; ES 2130212 T3 19990701; JP H06163201 A 19940610; TW 240321 B 19950211; US 5677070 A 19971014; US 5748069 A 19980505

DOCDB simple family (application)

EP 93201714 A 19930615; DE 59309376 T 19930615; ES 93201714 T 19930615; JP 14375993 A 19930615; TW 82107731 A 19930921; US 63932796 A 19960425; US 80552797 A 19970225